

033035 M 0342

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Kensaku MOTOKI, et al.

U.S. Serial No.: 10/691,569

Group Art Unit: 2814

Filed: October 24, 2003

Examiner: To Be Assigned

For: GaN Single Crystal Substrate and Method of Making the Same

THIRD INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:


Pursuant to the duty of disclosure under 37 C.F.R. 1.56, Applicants enclose an Information Disclosure Citation Form (PTO-1449) which lists documents cited in a Japanese Office Action (dated April 18, 2006) submitted herewith.

Applicants certify under 37 C.F.R. 1.97(e)(1) that all documents submitted herewith were first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this Statement. Therefore, it is respectfully urged that no fees are required for the Examiner's consideration of the documents listed in this Information Disclosure Statement.

It is respectfully requested that the cited documents be considered by the Examiner in the above-identified patent application and that the cited documents be made officially of record therein. It is further requested that a listing of the same appear on the face of any patent which may issue from this application.

Respectfully submitted,
SMITH, GAMBRELL & RUSSELL, LLP

By:


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| FORM PTO-1449 INFORMATION DISCLOSURE STATEMENT | ATTY. DOCKET 033035 M 0342 | SERIAL NO. 10/691,569 |
| | APPLICANT: Kensaku MOTOKI, et al. | |
| | FILING DATE October 24, 2003 | GROUP ART UNIT 2814 |

U.S. PATENT DOCUMENTS

| *Examiner's Initials | | DOCUMENT NUMBER | DATE | NAME | CLASS | SUB-CLASS | FILING DATE, IF APPROPRIATE |
|----------------------|----|-----------------|------|------|-------|-----------|-----------------------------|
| | AA | | | | | | |
| | AB | | | | | | |
| | AC | | | | | | |
| | AD | | | | | | |
| | AF | | | | | | |
| | AG | | | | | | |
| | AH | | | | | | |
| | AI | | | | | | |
| | AJ | | | | | | |
| | AK | | | | | | |

FOREIGN PATENT DOCUMENTS

| *Examiner's Initials | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUB-CLASS | TRANSLATION YES NO | |
|----------------------|----|-----------------|------------|---------|-------|-----------|-----------------------|--|
| | AL | 97/11518 | 3/27/1997 | WO | | | | |
| | AM | 07-273048 | 10/20/1995 | JAPAN | | | abstract | |
| | AN | 11-135770 | 5/21/1999 | JAPAN | | | abstract | |
| | AO | | | | | | | |
| | AP | | | | | | | |

OTHER INFORMATION (Including Author, Title, Date, Pertinent Pages, Etc.)

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|---|--|
| AQ | H. Okumura, et al., "Epitaxial growth of cubic and hexagonal GaN on GaAs by gas-source molecular-beam epitaxy", Appl. Phys. Lett. 59(9), August 26, 1991, pages 1058-1060, November 2002 |
| AR | K. Naniwae, et al., "Growth of Single Crystal GaN Substrate Using Hydride Vapor Phase Epitaxy", Journal of Crystal Growth 99, 1990, pages 381-384 |
| AS | Notice of Rejection from JPO |
| EXAMINER: | DATE CONSIDERED: |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | |